Advance Information N-Channel JFET –15 V, 10 to 32 mA, 35 mS, Dual

Automotive JFET designed for compact and efficient designs and including high gain performance. AEC-Q101 qualified JFET and PPAP capable suitable for automotive applications.

Features

- Large | yfs |
- Small Ciss
- This small package enables sets to be smaller and thinner
- Ultralow noise figure
- Pb-Free, Halogen Free and RoHS compliance
- MCPH5 package is pin-compatible with SC-88AFL
- AEC-Q101 qualified and PPAP capable
- Composite type with 2 JFET contained in a MCPH5 package currently in use, improving the mounting efficiency greatly
- The NSVJ5908DSG5 is formed with two chips, being equivalent to the NSVJ3557SA3, placed in one package

Typical Applications

- AM Tuner RF Amplification
- Low Noise Amplifier

SPECIFICATIONS

ABSOLUTE MAXIMUM RATINGS at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit	
Drain-to-Source Voltage	V _{DSX}	15	٧	
Gate-to-Drain Voltage	V _{GDS}	-15	٧	
Gate Current	IG	10	mA	
Drain Current	ID	50	mA	
Allowable Power Dissipation 1 unit	PD	200	mW	
Total Power Dissipation	PT	300	mW	
Operating Junction and Storage Temperature	T _{J,} T _{Stg}	-55 to +150	°C	

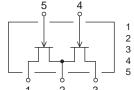
Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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ELECTRICAL CONNECTION N-Channel



- 1 : Drain1
- 2 : Source1/Source2
- 3 : Drain2
- 4 : Gate2
- 5 : Gate1



MARKING



ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet

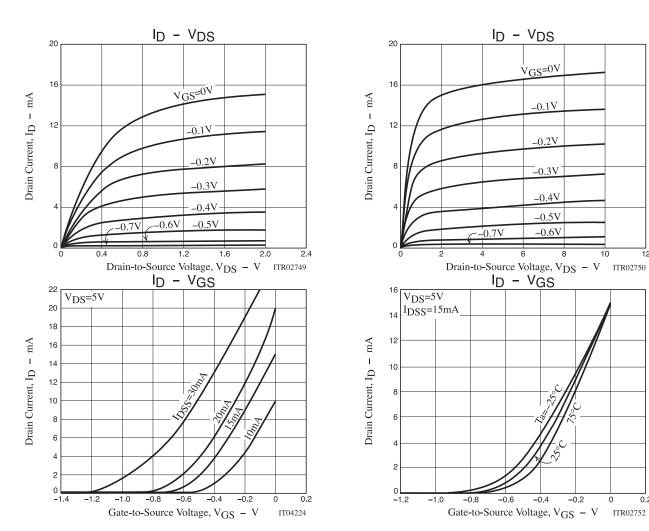
This document contains information on a new product. Specifications and information herein are subject to change without notice.

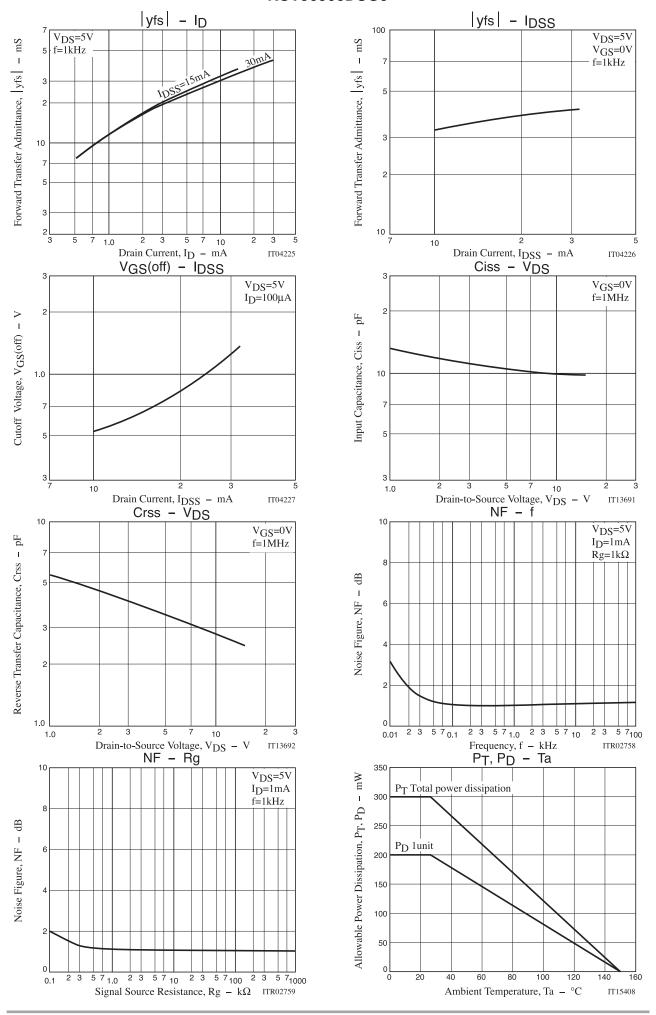
ELECTRICAL CHARACTERISTICS at Ta = 25°C (Notes 2,3)

Parameter	Cumbal	Conditions	Value			Unit
Farameter	Symbol	Conditions		typ	max	Offic
Gate-to-Drain Breakdown Voltage	V _{(BR)GDS}	$I_G = -10 \mu A, V_{DS} = 0 V$	-15			V
Gate-to-Source Leakage Current	IGSS	$V_{GS} = -10 \text{ V}, V_{DS} = 0 \text{ V}$			-1.0	nA
Cutoff Voltage	V _{GS(off)}	V _{DS} = 5 V, I _D = 100 μA	-0.3	-0.7	-1.5	V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} = 5 V, V _{GS} = 0 V	10		32	mA
Forward Transfer Admittance	yfs	$V_{DS} = 5 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ kHz}$	24	35		mS
Input Capacitance	Ciss	V _{DS} = 5 V, V _{GS} = 0 V, f = 1 MHz		10.5		pF
Reverse Transfer Capacitance	Crss	VDS - 3 V, VGS - 0 V, I - 1 WI12		3.5		pF
Noise Figure	NF	$V_{DS} = 5 \text{ V}, \text{ Rg} = 1 \text{ k}\Omega, \text{ I}_D = 1 \text{ mA},$ f = 1 kHz		1.0		dB

Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Note 3: The specifications shown above are for each individual JFET.



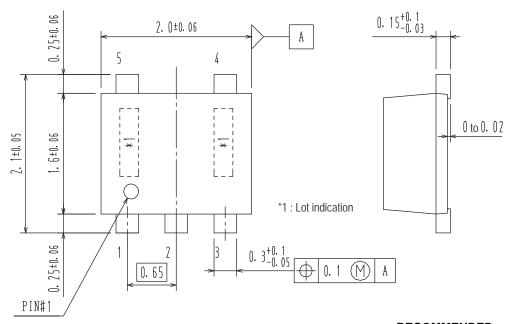


PACKAGE DIMENSIONS

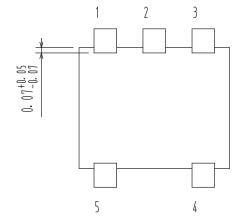
unit: mm

SC-88AFL / MCPH5

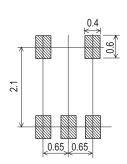
CASE 419AP ISSUE O



0.05 \$



RECOMMENDED SOLDERING FOOTPRINT



- 1: Drain1
- 2 : Source1/Source2
- 3 : Drain2
- 4 : Gate2
- 5 : Gate1

ORDERING INFORMATION

Device	Marking	Package	Shipping
NSVJ5908DSG5T1G	К	SC-88AFL / MCPH5 (Pb-Free / Halogen Free)	3,000 / Tape & Reel

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

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